IN THE SPECIFICATION:

Please amend the paragraph beginning at page 35, line 23, and ending at page 36, line 7, as follows:

--Preferably, the base member 101-1 is a plate-like member or a sheet-like member composed of metal, resin, glass, ceramics, or a semiconductor bulk. The surface of the base member may be provided with fine projections and recesses. The base member may be transparent so that light is incident from the base member side. Alternatively, the base member may be ~~elongate~~ elongated so as to allow a film to be continuously formed using the roll to roll process. In particular, flexible material such as stainless steel or polyimide is suitable as material for the base member 101-1.--

Please amend the paragraph beginning at page 70, line 2, and ending at page 70, line 19, as following:

--Then, ~~s source~~ a source gas and a diluting gas were supplied to the semiconductor formation vacuum vessels 211 to 218 through the gas introducing pipes 231 to 238 while operating the evacuation system. The discharge chambers in the semiconductor formation vacuum vessels 212 and 213 each had a longitudinal length of 1 m and a transverse width of 50 cm. The gas gates were supplied with 500-cm^3/min (normal) H_2 gas through gate gas supply pipes (not shown in the drawings) as gate gas. Under these conditions, the exhaust performance of the evacuation system was regulated to adjust the pressures in the semiconductor formation vacuum vessels 211 to 216 to predetermined values. Formation

conditions for the semiconductor formation vacuum vessels 211 to 215 were similar to those in Example 2-2. Formation conditions for the semiconductor formation vacuum vessels 216 to 218 are shown in Table 14.--